

ABSTRACT OF THE DISCLOSURE

In a semiconductor system 20 made up of multiple sublayers, a sublayer over the largest part of a cross-sectional area BC in the interior of the semiconductor system borders immediately
5 on the first sublayer, while bordering on a second sublayer only in a comparatively narrow edge region of the cross-sectional area. The semiconductor system is characterized by a low bulk resistance and a high breakdown voltage in the edge region. In addition, a method for manufacturing this
10 semiconductor system is specified.

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